XN0121E (XN121E)

Silicon NPN epitaxial planar type

For switching/digital circuits

Features

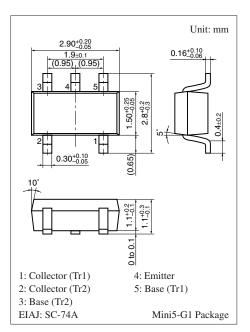
- Two elements incorporated into one package (Emitter-coupled transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

Basic Part Number

• UNR221E (UN221E) × 2

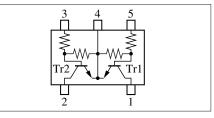
Absolute Maximum Hatings $T_a = 25$ C							
Parameter	Symbol	Rating	Unit				
Collector-base voltage (Emitter open)	V _{CBO}	50	V				
Collector-emitter voltage (Base open)	V _{CEO}	50	V				
Collector current	I _C	100	mA				
Total power dissipation	P _T	300	mW				
Junction temperature	Tj	150	°C				
Storage temperature	T _{stg}	-55 to +150	°C				

Absolute Maximum Ratings $T_a = 25^{\circ}C$



Marking Symbol: AQ

Internal Connection

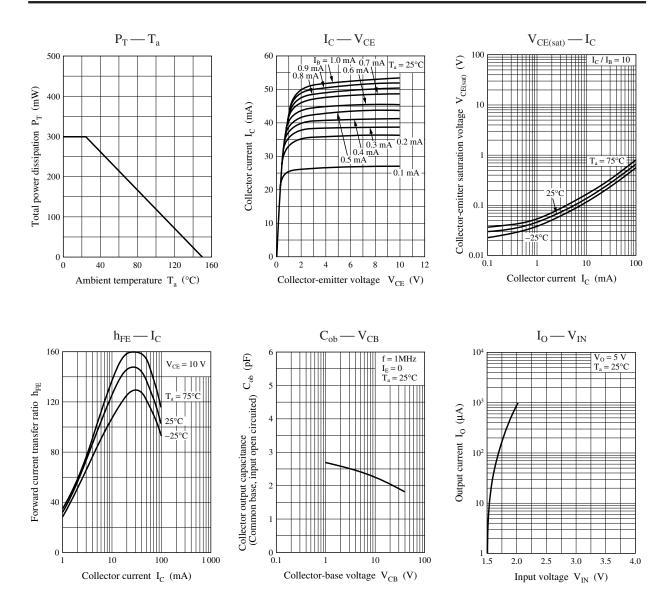


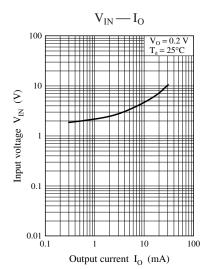
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 10 \ \mu A, \ I_{\rm E} = 0$	50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 2 \text{ mA}, I_{\rm B} = 0$	50			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = 50 \text{ V}, I_E = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 50 \text{ V}, I_B = 0$			0.5	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = 6 V, I_C = 0$			0.2	mA
Forward current transfer ratio	h _{FE}	$V_{CE} = 10 \text{ V}, I_C = 5 \text{ mA}$	60			_
h _{FE} Ratio *	h _{FE(Small}	$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$	0.50	0.99		
	/Large)					
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{C} = 10 \text{ mA}, I_{B} = 0.3 \text{ mA}$			0.25	V
Output voltage high-level	V _{OH}	$V_{CC} = 5 \text{ V}, \text{V}_{\text{B}} = 0.5 \text{V}, \text{R}_{\text{L}} = 1 \text{k} \Omega$	4.9			V
Output voltage low-level	V _{OL}	$V_{CC} = 5 V, V_B = 6 V, R_L = 1 k\Omega$			0.2	V
Input resistance	R ₁		-30%	47	+30%	kΩ
Resistance ratio	R ₁ / R ₂			2.14		_
Transition frequency	f _T	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		150		MHz

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: Ratio between 2 elements

Note) The part number in the parenthesis shows conventional part number.





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